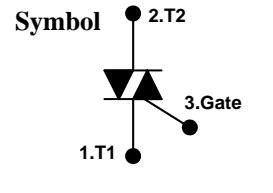


HTx2-600

V_{DRM} = 600 V
 $I_{T(RMS)}$ = 2.0A



1.T1 2. T2 3. Gate



HTC2-600



HTM2-600

FEATURES

- Repetitive Peak Off-State Voltage: 600V
- R.M.S On-state Current ($I_{T(RMS)}=2A$)
- High Commutation dv/dt

General Description

The Triac HTx2-600 is suitable for AC switching application, phase control application such as heater control, motor control, lighting control, and static switching relay.

Absolute Maximum Ratings $(T_a=25^\circ\text{C})$

Symbol	Parameter	Value	Units
V_{DRM}	Repetitive Peak Off-State Voltage	600	V
$I_{T(RMS)}$	R.M.S On-State Current ($T_a = 66^\circ\text{C}$)	1.5	A
I_{TSM}	Surge On-State Current (One Cycle, 50/60Hz, Peak, Non Repetitive)	13/15	A
V_{GM}	Peak Gate Voltage	6	V
I_{GM}	Peak Gate Current	0.5	A
P_{GM}	Peak Gate Power Dissipation	1	W
T_{STG}	Storage Temperature Range	-40 to +125	°C
T_j	Operating Temperature Range	-40 to +125	°C

Electrical Characteristics (T_a=25°C)

Symbol	Parameter	Test Conditions		Min	Typ	Max	Units
I _{GT}	Gate Trigger Current	V _D =6V, R _L =10Ω	1+, 1-, 3-			20	mA
V _{GR}	Gate Trigger Voltage	V _D =6V, R _L =10Ω	1+, 1-, 3-			1.5	V
V _{GD}	Non Trigger Gate Voltage	T _j =125°C, V _D =1/2V _{DRM}		0.2			V
(dv/dt) _C	Critical Rate of Rise of Off-State Voltage at Communication	T _j =125°C, V _D =2/3V _{DRM} (di/dt) _C =-0.75A/ms		5			V/uS
I _H	Holding Current				5		mA
I _{DRM}	Repetitive Peak Off-State Current	V _D =V _{DRM} , Single Phase, Half Wave, T _j =125°C				0.5	mA
V _{TM}	Peak On-State Voltage	I _T =6A, Inst, Measurement				1.6	V

Thermal Characteristics

Symbol	Parameter	Test Conditions		Min	Typ	Max	Units
R _{TH(J-C)}	Thermal Resistance	Junction to Case				6.25	°C/W

Performance Curves

Fig 1. Gate Characteristics

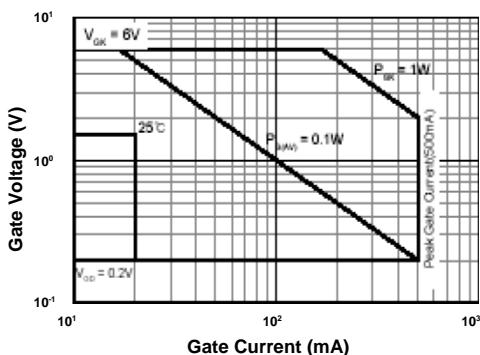


Fig 2. On-State Voltage

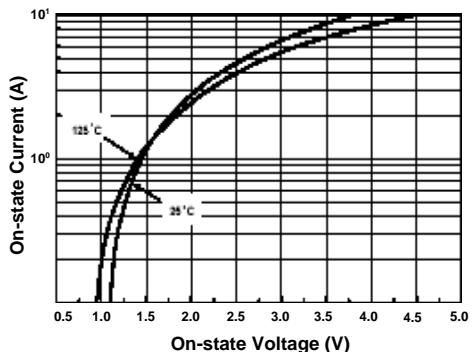


Fig 3. Gate Trigger Voltage vs. Junction Temperature

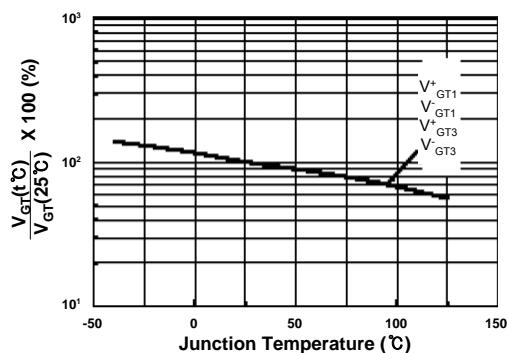


Fig 4. On State Current vs. Maximum Power Dissipation

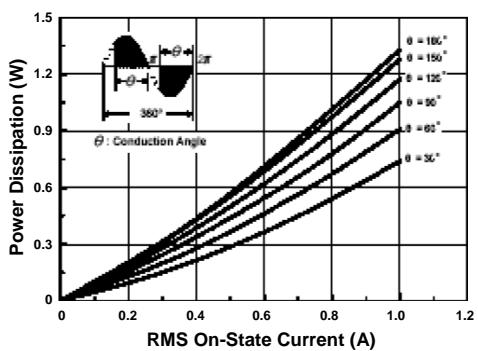


Fig 5. On State Current vs. Allowable Case Temperature

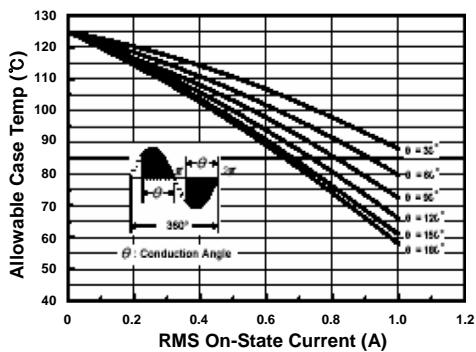


Fig 6. Surge On-State Current Rating (Non-Repetitive)

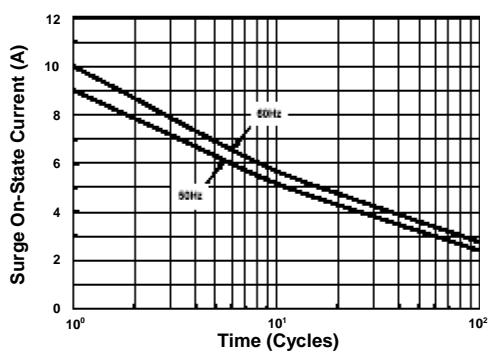


Fig 7. Gate Trigger Current vs. Junction Temperature

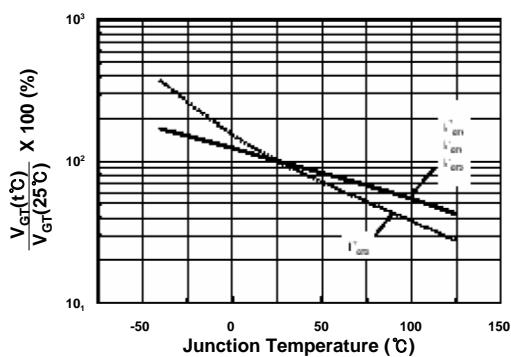


Fig8. Transient Thermal Impedance

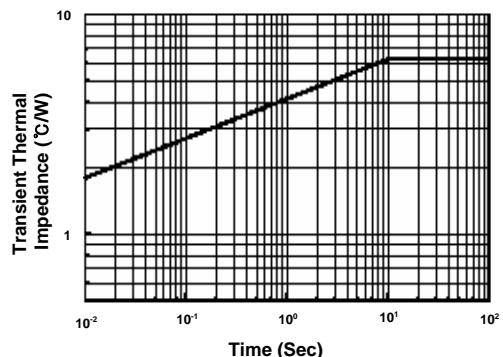
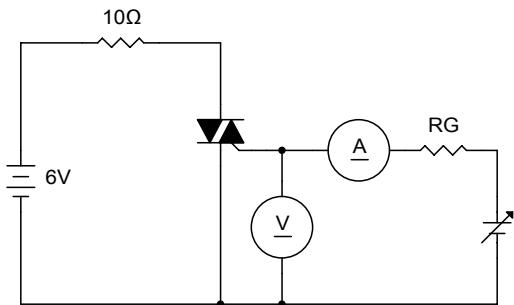
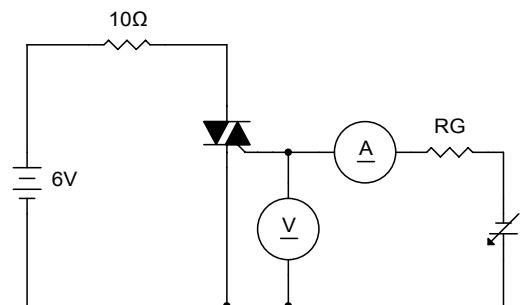


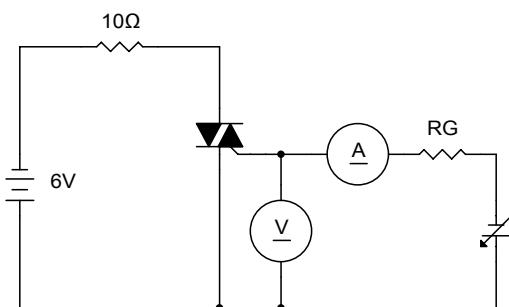
Fig 7. Gate Trigger Characteristics Test Circuit



Test Procedure I



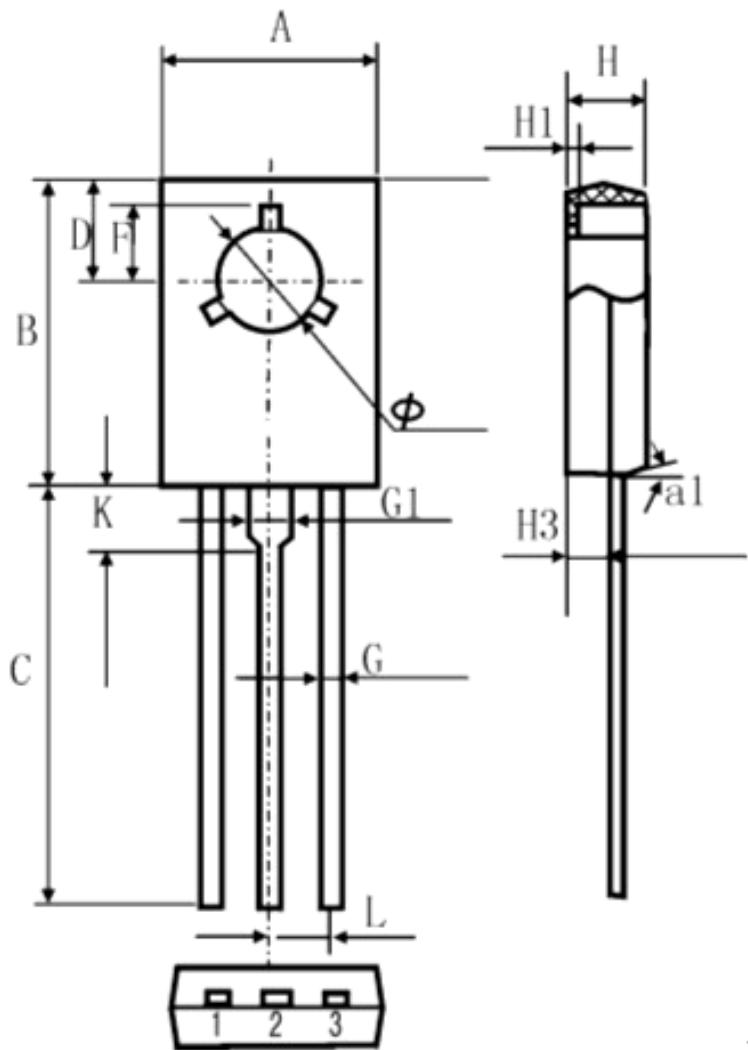
Test Procedure II



Test Procedure III

Package Dimension**HTC2-600
(TO-126)**

DIM	Millimeters
A	8.5max
B	12.0max
C	13.0min
D	3.8 ± 0.2
G	0.78 ± 0.08
G1	1.2
H	2.8max
H3	1.27
K	2.5 ± 0.2
L	2.3max
ϕ	3.20 ± 0.2



Dimensions in Millimeters

Package Dimension**HTM2-600
(TO-126ML)**

corresponding symbol	measurement
A(mm)	7.99±0.25
B(mm)	11.12±0.25
C(mm)	14.5±0.5
E(mm)	3.625±0.125
F(mm)	1.4±0.12
G(mm)	0.76±0.08
G1(mm)	1.3±0.12
H(mm)	3.57±0.13
H3(mm)	2.01±0.13
I(mm)	2.99±0.38
K(mm)	1.0±0.12
L(mm)	2.3MAX
Φ1(mm)	3.0±0.12

